



216111US2X

#9/A
10/28/02
Haye
RECEIVED
OCT 17 2002
TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: :
Kenji FUKUDA, et al. : GROUP ART UNIT: 2815
SERIAL NO.: 09/987,271 :
FILED: NOVEMBER 14, 2001 : EXAMINER: NGUYEN, J.
FOR: SiC SEMICONDUCTOR :
DEVICE :

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated April 12, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 1 and 17 without prejudice or disclaimer.

Please amend Claims 2 and 8-16 as shown in clean form below:¹

- Sub
A' B' →
2. (Amended) A SiC semiconductor device comprising:
- a semiconductor substrate having a P-type silicon carbide region, a gate insulation layer formed on the silicon carbide region;
 - an effective P-type gate electrode formed on the gate insulation layer, an N-type impurity region having an impurity concentration sufficient to form a buried channel region

¹A marked-up copy of the amendments to the claims is attached hereto.